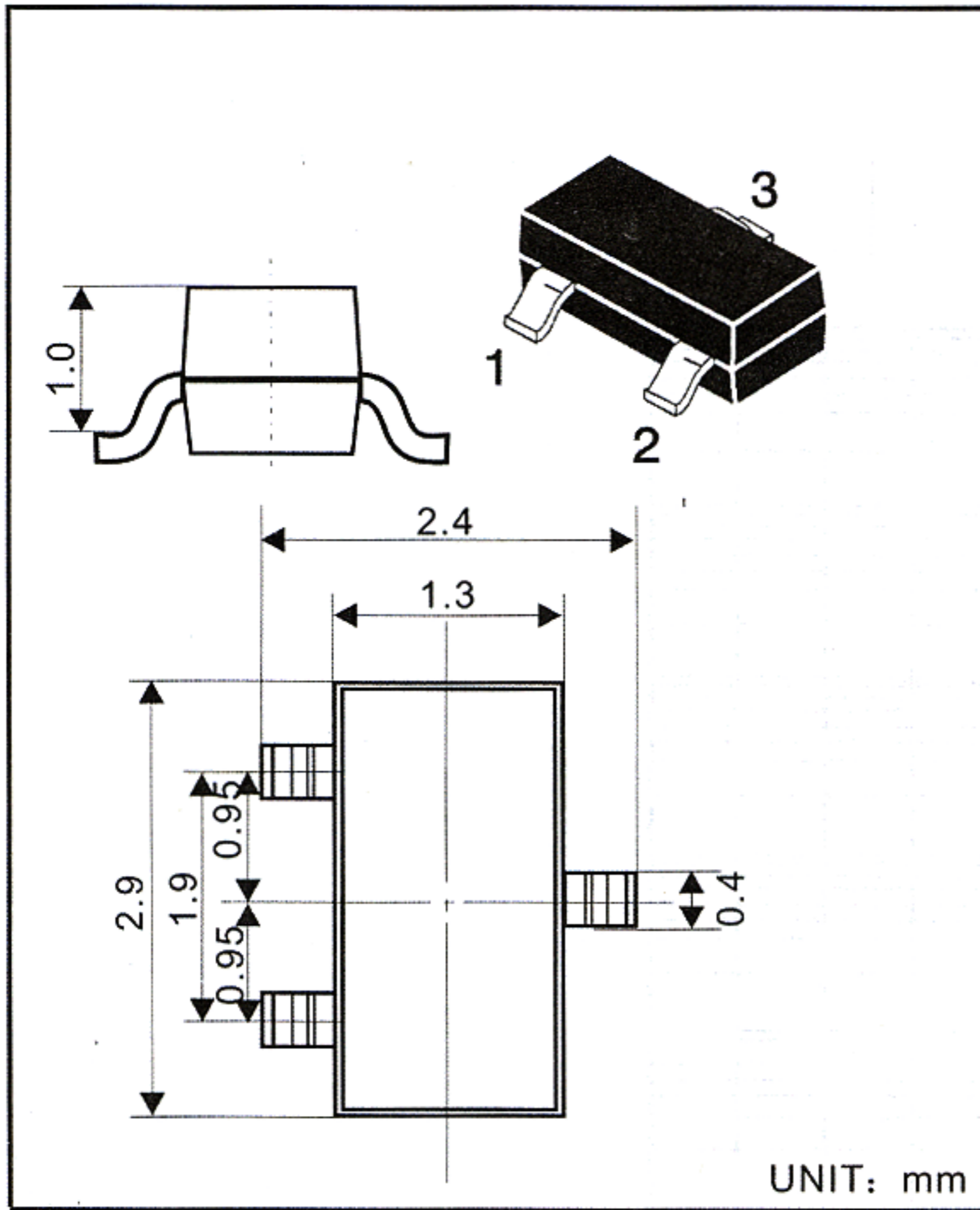


## BAS40 SERIES SCHOTTKY DIODE



### FEATURES

#### Power dissipation

$P_D$ : 200mW ( $T_{amb}=25^\circ\text{C}$ )

#### Forward current

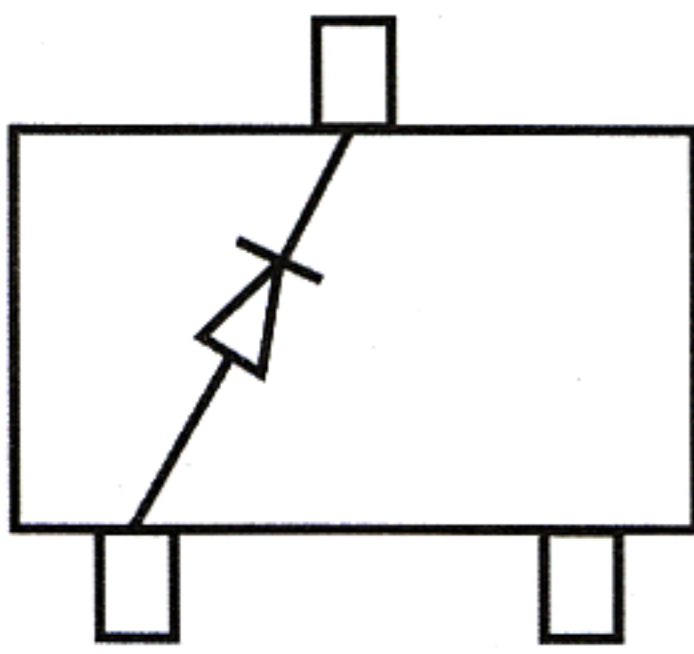
$I_F$ : 200mA

#### Reverse voltage

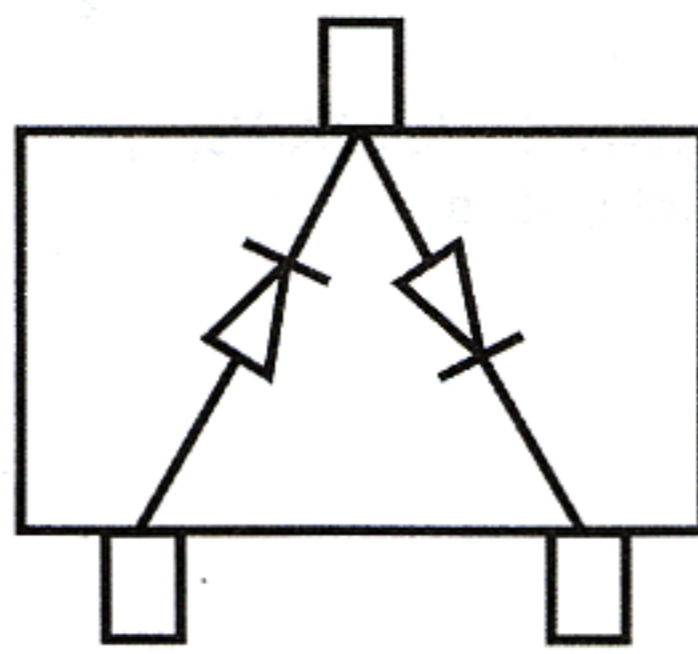
$V_R$ : 40V

#### Operating and storage junction temperature range

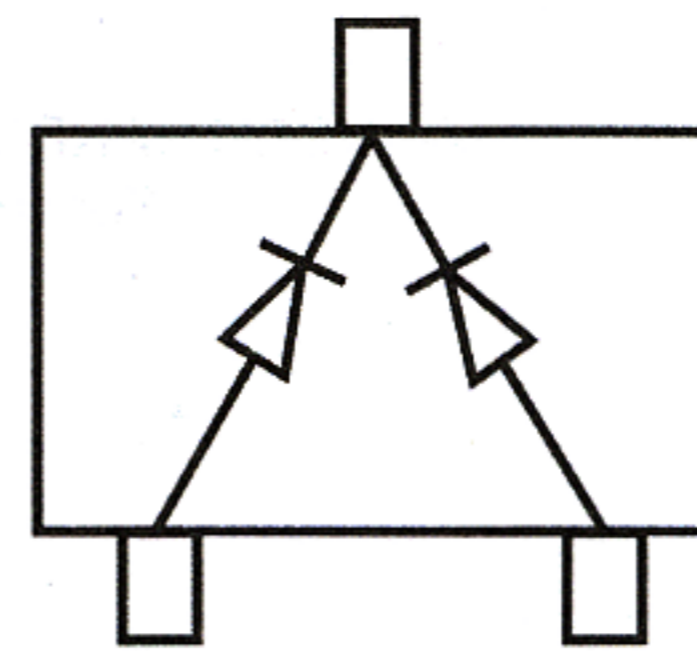
$T_J, T_{stg}$ :  $-55^\circ\text{C}$  to  $+150^\circ\text{C}$



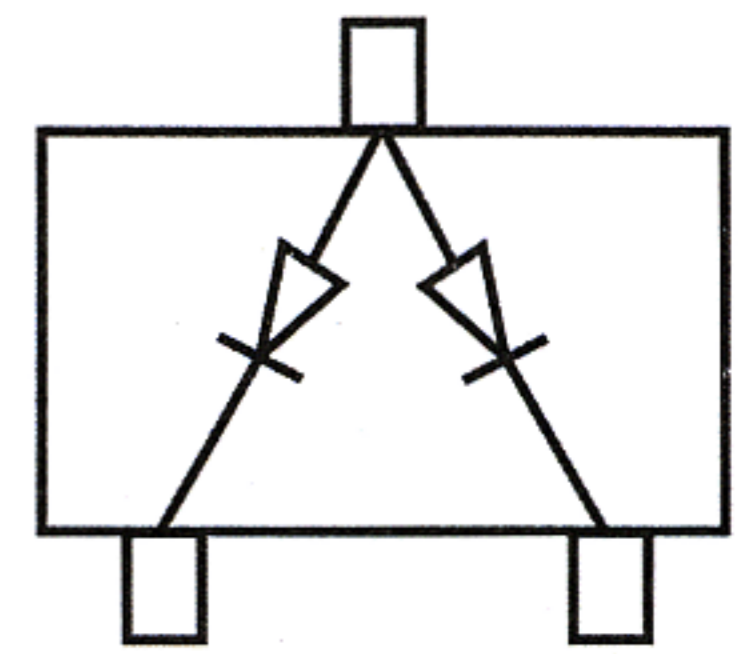
BAS40 MARKING: 43



BAS40-04 MARKING: 44



BAS40-05 MARKING: 45



BAS40-06 MARKING: 46

### ELECTRICAL CHARACTERISTICS

( $T_{amp}=25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\ \mu\text{A}$	40		V
Reverse voltage leakage current	$I_R$	$V_R=30\text{V}$		2	$\mu\text{A}$
Forward voltage	$V_F$	$I_F=1\text{mA}$ $I_F=40\text{mA}$		380 1000	mV
Diode capacitance	$C_{tot}$	$V_R=0\text{V}, f=1\text{MHz}$		5	pF
Reverse recovery time	$t_{rr}$	$I_F=I_R=10\text{mA}$ $I_{rr}=0.1I_R$		5	ns



